

54F38

Microcircuits, Digital, Bipolar Advanced Schottky TTL, NAND Buffers

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer (OCM).

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
 - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

INCH-POUND

MIL-M-38510/352A

16 June 2004

SUPERSEDING

MIL-M-38510/352

7 August 1987

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, BIPOLAR ADVANCED SCHOTTKY TTL, NAND BUFFERS, MONOLITHIC SILICON

Reactivated after 16 June 2004 and may be used for either new or existing design acquisition.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product herein shall consist of this specification sheet and MIL-PRF 38535

- 1. SCOPE
- 1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, Advanced Schottky TTL, NAND buffers. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).
 - 1.2 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-38535, and as specified herein.
 - 1.2.1 <u>Device types.</u> The device types are as follows:

<u>Jevice type</u>	Circuit
01	Quad 2-input NAND buffer
02	Quad 2-input NAND buffer (open collector)
03	Dual 4-input NAND buffer

- 1.2.2 Device class. The device class is the product assurance level as defined in MIL-PRF-38535.
- 1.2.3 Case outlines. The case outlines are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

Comments, suggestions, or questions on this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, P. O. Box 3990, Columbus, OH 43218-3990, or emailed to bipolar@dscc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at www.dodssp.daps.mil.

AMSC N/A FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range Input voltage range Storage temperature range Maximum power dissipation, per device (P _D) 1/	-1.2 V dc at -18 mA to +7.0 V dc
Device type 01	182 m\\/
Device type 01	
Device type 03	
Lead temperature (soldering, 10 seconds)	
Thermal resistance, junction to case (θ_{JC}):	. 555 6
Cases C, D, and 2	(See MIL-STD-1835)
Junction temperature (T _.) 2/	·

1.4 Recommended operating conditions.

Supply voltage	4.5 V dc minimum to 5.5 V dc
,	maximum
Minimum high level input voltage (V _{IH})	2.0 V dc
Maximum low level input voltage (V _{IL})	0.8 V dc
Normalized fanout (each output) 3/:	
Low level 01, 03	80 maximum
Low level 02	16 maximum
High level 01, 03	50 maximum
High level 02	12 maximum
Case operating temperature range (T _C)	-55° to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>General.</u> The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 <u>Specifications and Standards</u>. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard for Microelectronics.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or www.dodssp.daps.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

^{1/} Must withstand the added P_D due to short-circuit test (e.g., I_{OS}).

Maximum junction temperature should not be exceeded except in accordance with allowable short duration burn-in screening condition in accordance with MIL-PRF-38535.

^{3/} The device should fanout in both high and low levels to the specified number of inputs of the same device type as that being tested.

2.3 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).
- 3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.
- 3.3.1 <u>Terminal connections and logic diagrams</u>. The terminal connections and logic diagrams shall be as specified on figure 1.
 - 3.3.2 Truth tables. The truth tables shall be as specified on figure 2.
- 3.3.3 <u>Schematic circuits.</u> The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.
 - 3.3.4 Case outlines. The case outlines shall be as specified in 1.2.3.
 - 3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).
- 3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.
- 3.6 <u>Electrical test requirements</u>. The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.
 - 3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.
- 3.8 <u>Microcircuit group assignment.</u> The devices covered by this specification shall be in microcircuit group number 9 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

- 4.1 <u>Sampling and inspection.</u> Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.
- 4.2 <u>Screening.</u> Screening shall be in accordance with MIL-PRF-38535 and shall be conducted on all devices prior to qualification and conformance inspection. The following additional criteria shall apply:
 - a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
 - c. Additional screening for space level product shall be as specified in MIL-PRF-38535.

TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol	Conditions	Device	Lin	nits	Unit
		-55°C ≤ T _C ≤ +125°C	type	Min	Max	
		unless otherwise specified				
High level output voltage	V_{OH}	$V_{CC} = 4.5 \text{ V}, V_{IL} = 0.8 \text{ V},$	01, 03	2.5		V
		$I_{OH} = -1 \text{ mA}, V_{IH} = 2.0 \text{ V}$				
Low level output voltage	V_{OL}	$V_{CC} = 4.5 \text{ V}, I_{OL} = 48 \text{ mA},$	All		0.55	V
		$V_{IH} = 2.0 \text{ V}, V_{IL} = 0.8 \text{ V}$				
Input clamp voltage	VIC	$V_{CC} = 4.5 \text{ V}, I_L = -18 \text{ mA},$	All		-1.2	V
		T _C = +25°C				
High level input current	I _{IH1}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 2.7 \text{ V}$	All		20	μΑ
	I _{IH2}	V _{CC} = 5.5 V, V _{IN} = 7.0 V	All		100	μΑ
Low level input current	I _{IL1}	V _{CC} = 5.5 V, V _{IL} = 0.5 V	All	0	-1.2	mA
Short circuit output	Ios	V _{CC} = 5.5 V, V _{OS} = 0.0 V	01, 03	-100	-225	mA
current <u>1</u> /						
Maximum collector cut-off current	I _{CEX}	$V_{CC} = 4.5 \text{ V}, V_{IN} = 0.8 \text{ V},$	02		250	μΑ
Supply current	I _{CCL}	V _{CC} = 5.5 V	01		33	mA
			02		30	
			03		17	
	I _{CCH}		01		6	mA
			02		7	
			03		4	
Propagation delay time,	t _{PHL}	$V_{CC} = 5.0 \text{ V}, C_L = 50 \text{ pF} \pm 10\%,$	01	1.0	5.5	ns
high-to-low level		R _L = see figure 3	02	1.0	6.0	
			03	1.0	5.5	
Propagation delay time,	t _{PLH}		01	1.5	7.0	ns
low to high level			02	6.5	14.5	
			03	1.0	6.5	

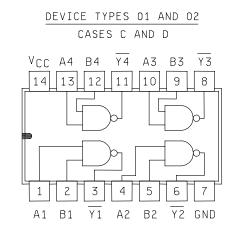
 $[\]underline{1}$ / Not more than one output should be shorted at a time.

TABLE II. Electrical test requirements.

	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 9, 10, 11	1*, 2, 3, 9
Group A test requirements	1, 2, 3, 7, 9, 10, 11	1, 2, 3, 7, 9, 10, 11
Group B electrical test parameters when using the method 5005 QCI option	1, 2, 3, 9, 10, 11	N/A
Group C end-point electrical parameters	1, 2, 3, 9, 10, 11	1, 2, 3
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

^{*}PDA applies to subgroup 1.

- 4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-38535.
- 4.4 <u>Technology Conformance inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).
- 4.4.1 <u>Group A inspection.</u> Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 4, 5, 6, and 8 shall be omitted.
 - 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.
- 4.4.3 <u>Group C inspection.</u> Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- 4.4.4 <u>Group D inspection.</u> Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.
 - 4.5 Methods of inspection. Methods of inspection shall be specified as follows:
- 4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.



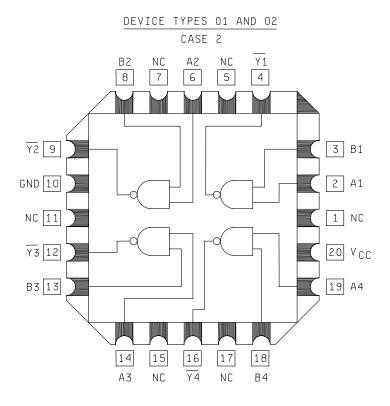
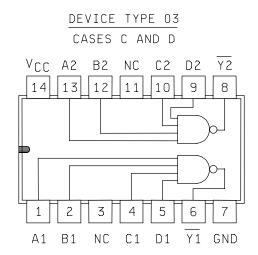


FIGURE 1. Terminal connections and logic diagram (top view).



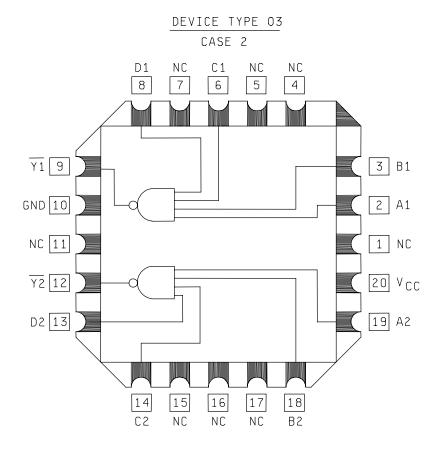


FIGURE 1. <u>Terminal connections and logic diagram</u> Continued.

Device type 01 and 02

Inp	outs	Output
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

H = High level L = Low level

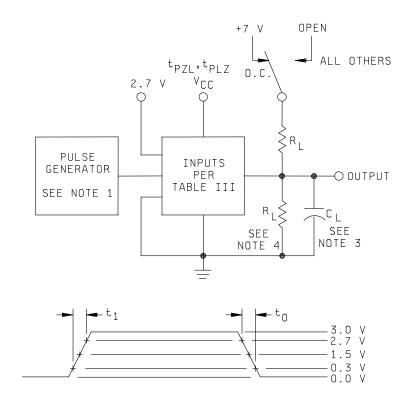
Device type 03

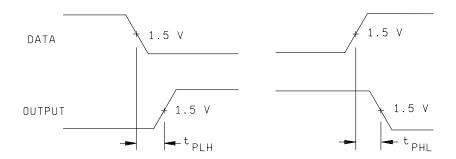
	Inp	uts		Output
Α	В	С	D	Υ
L	Х	Х	Х	Н
Х	L	X	X	Н
Х	X	L	X	Н
Х	Х	Х	L	Н
Н	Н	Н	Н	L

H = High level L = Low level

x = Immaterial

FIGURE 2. Truth tables.





NOTES:

- 1. Pulse generator has the following characteristics:
 - $t_1 = t_0 \leq 2.5 \text{ ns, PRR} \leq 1 \text{ MHz, } Z_{OUT} \cong 50\Omega.$
- 2. Inputs not under test are at ground or 2.7 V as specified in table III.
- 3. $C_L = 50 \text{ pF} \pm 10\%$, including scope probe, wiring and stray capacitance without package in test fixture.
- 4. $R_L = 499\Omega \pm 5\%$.
- 5. Voltage measurements are to be made with respect to network ground terminal.

FIGURE 3. Switching time test circuit and waveforms for all device types.

TABLE III. Group A inspection for device type 01. Terminal conditions (pins not designated may be high ≥ 2.0 V or low ≤ 0.8 V or open).

	Unit		>	=	=	=	=	=	=	=	=		=	=	=	=	=	=	=	=	=	= :	- -	: =	=	Αμ	=	= =	=	=	=			= :	- -	=	=	=	=
	its	Max									0.55	ıı	ıı.	u	=	=	=	=	-1.2	u	=	= :		: :	=	20	=			=			100	- :		=	=	=	
	Limits	Min	2.5		н	=	=																																
	Measured terminal	•	17	17	<u>Y2</u>	<u>Y2</u>	<u>73</u>	/3	<u>74</u>	<u>γ</u>	17	71	<u>77</u>	<u>77</u>	<u>73</u>	<u>\73</u>	_ \		A1	B1	A2	B2	B3	A3	44 Z	A1	B1	A2	B3	A3	B4	A4	A1	B1	A2	B3	A3	B4	A4
14	20	Vcc	4.5 V	=		=	=	=	=	=	=	н	н	=	=	=	:	=	=	=	=	= :		: =	=	5.5 V	=		=	=	=		н	= :		=	=	=	=
13	19	A4	5.5 V	=	=	=	=	=	0.8 V	5.5 V	=	"	н		=	=	2.0 V	5.5 V	=	=	=	=		: =	-18 mA							2.7 V							7.0 V
12	18	B4	5.5 V	=	=	=	=	=	=	0.8 V	5.5 V	ш	"		=	=	=	2.0 V	5.5 V	=	=	=		-18 m A	+-						2.7 V							7.0 V	
11	16	 	4,						-1.0 mA	-1.0 mA	47						48 mA	48 mA	4)					7	4,						.,					+			
10	14	A3	5.5 V	=		_	0.8 V	5.5 V	-1.	-1.					2.0 V	5.5 V	1 48		_	_	_	_		-18 mA 5 5 V	> >					2.7 V						+	7.0 V		_
							3.0		>						2.0														>	-	i					>	-		
6	13	B3	5.5 V	=	=	=	" Ar	V 8.0	5.5 V	=	=	н			<u>.</u>	A 2.0 V	5.5 V	=	=	=	=	=	-18 mA	5.5 \	=			1	27.7							7.0 V		H	_
8	12	<u>73</u>					-1.0 mA	-1.0 mA							48 mA	48 mA																				\downarrow			
7	10	GND	GND	"	n	3	3	n	n	3	=	n		n	31	n	3	3	n	33	я	3	3 3	: 3	3	n	3	= =	n	n	3	n	n	3 3	: :	3	з	n	n
9	6	<u>77</u>			-1.0 mA	-1.0 mA							48 mA	48 mA																									
2	8	B2	5.5 V	5.5 V	0.8 V	5.5 V	=					"	2.0 V	5.5 V					"	ıı	"	-18 mA	5.5 V	: =	=			277	Z. / V						707	۷.0.۷			
4	9	A2	5.5 V	=	=	0.8 V	5.5 V	=	=	=	=			2.0 V	5.5 V	=	=	=				5.5 V		: -	=			2.7 V							7.0 /				
ю	4	ΙΣ	-1.0 mA	-1.0 mA							48 mA	48 mA																											
2	က	B1	0.8 V	5.5 V -1	=	=	=	=	=	=		5.5 V		=	=	=	=	=	=	-18 mA	5.5 V	= :		: =	=		2.7 V							7.0 V		+			_
-	2	A1	5.5 V (0.8 V	5.5 V	=	=	_	=				5.5 V		=	=	-	=	_			= :		: =	=	2.7 V	.,						7.0 V			+			
se C	7		5.	Ö	5.																															+		H	_
Cases C.D	Case <u>1/</u>	Test no.	7	2	3	4	2	9	7	∞	6	10	11	12	13	14	15	16	17	18	19	20	21	23 62	24	25	26	27	000	30	31	32	33	8	32	37	38	39	40
MIL-STD-	883 method		3006	=	=	=	=	=	=	=	3007	=	=	=	=	=	=	=								3010	= :	= =	=	=	=		=	= :		=	=	=	=
	Symbol		V _{ОН}								Vol								Vıc							-H							ПН2						
	Subgroup		-	$Tc = 25^{\circ}C$																																			

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 01 - Continued.

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 02. Terminal conditions (pins not designated may be high ≥ 2.0 V or low ≤ 0.8 V or open).

	Unit		>	=	=	=	=	=	=	=	=	=	=	=	=			=	μĄ		=	=	=	=	=	=	=	=	=	=	=	=	=	=	mA	=	=	=	=	=	=	=
	ς,	Max	0.55	=	=	=	=	=	=	=	-1.2		=			u			20							=	100	=	=	=	=	=		=	2/	=		=	=	=	=	=
	Limits	Min																																	2/	=	н	=		=	=	=
	Measured		ΙĘ	ΙΣ	<u>72</u>	<u>72</u>	<u>\</u>	<u>√3</u>	7 4	7 4	A1	B1	A2	B2	B3	A3	B4	A4	A1	B1	A2	B2	B3	A3	B4	A4	A1	B1	A2	B2	B3	A3	B4	A4	A1	B1	A2	B2	B3	A3	B4	A4
14	20	Vcc	4.5 V	=	=	=	=	=	=	=		"				II	ш		5.5 V	"	"	"	=	"			=	=	=	=	=	=		=	=	=	"	=	=	=	=	=
13	19	A4	5.5 V	=	=	=	=	=	2.0 V	5.5 V		ш				"	11	-18 mA								2.7 V								7.0 V	5.5 V	=	"		=	=	=	0.5 V
12	18	B4	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V	н	н				-18 mA								2.7 V								7.0 V		5.5 V	=	н	=		=	0.5 V	5.5 V
1	16	<u>γ</u>							48 mA	48 mA																																
10	41	A3	5.5 V	=	=	=	2.0 V	5.5 V	"	"	ш		=	"		-18 mA	5.5 V	5.5 V						2.7 V								7.0 \			5.5 V	=		=	=	0.5 V	5.5 V	5.5 V
6	13	B3	5.5 V	=	=	=	=	2.0 V	5.5 V	=			=	=	-18 mA								2.7 V								7.0 V				5.5 V	=		=	0.5 V	5.5 V	=	-
∞	12	<u>73</u>					48 mA	48 mA																																		
7	10	GND	GND	n	n	я	n	31	n	n	n	п	n	и	п	11	n	11	11	n	n	n	n	п	11	11	n	n	n n	n	11	n	n	n	"	31	n	n	n	n	я	ņ
9	6	<u>Y2</u>			48 mA	48 mA																																				
2	8	B2	5.5 V	5.5 V	2.0 V	5.5 V	=	=	=	=	и			-18 mA	5.5 V		11					2.7 V								7.0 V					5.5 V	=	"	0.5 V	5.5 V	=	=	=
4	9	A2	5.5 V	=	=	2.0 V	5.5 V	=	=	=	"		-18 mA	-	-		"				2.7 V								7.0 V						5.5 V	5.5 V	0.5 V	5.5 V	=	=	=	=
3	4	۱۶	48 mA	48 mA									•																													
2	ဗ	B1	2.0 V	5.5 V	=	=	=	=	=	=		-18 mA	5.5 V	=						2.7 V								7.0 V							5.5 V	0.5 V	5.5 V	=		=	=	=
-	2	A1	5.5 V	2.0 V	5.5 V	=	=	=	=	=	_	5.5 V		=			н	н	2.7 V								7.0 V									H		=		=	=	=
Cases C.D	Case <u>1</u> / 2	Test no.	-	2	3	4	2	9	7	8			11	12	13	14	15			18	19	20	21	22	23	24		56	27	28	29	30	31				35	36	37	38	39	40
MIL-STD-		<u> </u>	3006	=	=	=	=	=	=	=									3010	=	=	=	=	=	=	=	=	=	=	=	=	=	=		3009	=	=	=	=	=	=	
	Symbol		Мон								Vıc								III								IH2								1							
	Subgroup		-	Tc = 25°C																						I																

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 02 – Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V or low ≤ 0.8 V or open).

	Unit		Αμ	=	=	=	=	=	=	=	mA.	Ψ						su	я	=	=	=	=	=	=	3	=	=	=	=	=	=	n	
	Limits	Мах	250	=	=	=	=	=	=	=	30	7						12.5	n	=	=	=	=	=	=	2.0	=	=	=	=	=	=	=	
	μij	Min																6.5	n	=	=	=	=	=	=	1.0	=	=	=	=	=	=	n	
	Measured terminal		77	<u>77</u>	<u>Y2</u>	<u>77</u>	<u> </u>	<u> </u>	<u>74</u>	<u>74</u>	Vcc	Vcc		W	outputs	н		A1 to 71	B1 to ₹1	A2 to <u>Y2</u>	B2 to <u>Y2</u>	A3 to <u>Y3</u>	B3 to <u>Y3</u>	A4 to <u>Y4</u>	B4 to <u>Y4</u>	A1 to 71	B1 to ₹1	A2 to <u>Y2</u>	B2 to <u>Y2</u>	A3 to <u>Y3</u>	B3 to <u>Y3</u>	A4 to <u>Y4</u>	B4 to <u>Y4</u>	
4	20	Vcc	4.5 V	=	=	=	=	=	=	=	5.5 V	5.5 V		3/	=			5.0 V	=	=	=	=	=	=	=	=	=	=	=	=	=	=	=	
13	19	A4	5.5 V	=	=	=	=	=	0.8 V	5.5 V	5.5 V	0.0 V		В	4	В	Α							Z	2.7 V							Z	2.7 V	
12	18	B4	5.5 V	=	=	=	=	=	=	0.8 V	5.5 V	0.0 V		В	В	А	Α							2.7 V	Z							2.7 V	Z	
=	16	<u>Y4</u>							4.5 V	4.5 V				I	=		L							OUT	OUT							OUT	OUT	
10	41	A3	5.5 V	=	=	=	0.8 V	5.5 V	=	=	=	0.0 V		В	۷	В	Α					Z	2.7 V							Z	2.7 V			
<u></u>	13	B3	5.5 V	=	=	=	=	0.8 V	5.5 V	=	=	0.0 V		В	В	Α	Α					2.7 V	Z							2.7 V	Z			
ω	12	<u> </u>					4.5 V	4.5 V					illed.	_ 	=		٦					OUT	OUT							OUT	OUT			
	10	GND	GND	n	n	y	a	n	n	n	n :	" "	except $1c = +125$ C and v_{1c} tests are difficted except $T_{c} = 55^{\circ}$ C and V_{c} tests are omitted	OND H B B	я	n	u	GND	n	=		=	=	=	=	3	=	=	E		=	=	ä	$_{\rm C} = +125^{\circ}$ C and use limits from table I
9	6	<u>Y2</u>			4.5 V	4.5 V							A Viotests	- -	=					OUT	OUT							OUT	OUT					se limits fr
2	8	B2	5.5 V	=	=	0.8 V	5.5 V	=	=	=	=	0.0 V	+123-C	В	В	Α	Α			2.7 V	Z							2.7 V	Z					$\Gamma_{\rm c}$ = +125° C and us
4	9	A2	5.5 V	5.5 V	0.8 V	5.5 V	=	=	=	=	H	0.0 V	cept Ical	B	4	В	Α			Z	2.7 V							Z	2.7 V					;= +125°
m	4	 	4.5 V	4.5 V								- 6	oup 1, ex) - - -			Γ	OUT	OUT							OUT	OUT							
2	ဇ	B1	V 8.0	5.5 V	=	=	=	=	=	=	=	0.0 V	for subar	B	В	А	Α	2.7 V	Z							2.7 V	Z							group 9,
_	2	A1	5.5 V 0		5.5 V	=	=	=	=	=		0.0 V 0.0	limits as	В	∢	В		N Z	2.7 V							Z	2.7 V							as for suk
ses D	/T ~ .	Test no.		42 0	43 5	44	45	46	7	48		50 0	litions and	51	2	53	4	2	56 2	7	58	29	09	-	2	63	64 2	65	99	7	89	69	20	onditions
Cases O- C.D	-	Test	41	4.	4	4	4	4	47	4	4	5	inal cond	5	5	5	2	2	3	22	5	Ω	9	61	62	9	9	9	Ø	29	9	9	7	rminal c
MIL-STD.			3009	=	=	=	=	=	=	=	3005	3005	Same tests, terminal conditions and limits as for subgroup 1, e	3014	=	=	=	3003	Fig. 3	=	=	=	=	=	=	=	=	=	=	=	=	=	=	Same tests and terminal conditions as for subgroup 9, except
	Symbol		lcex								lccr	POCH Specific	Same	Func	tional	tests	/₹	фгн								фн								Same to
	Subgroup		-	$Tc = 25^{\circ}C$								c	v (د	7	Tc = 25°C			6	$Tc = 25^{\circ}C$															10

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 03. Terminal conditions (pins not designated may be high ≥ 2.0 V or low ≤ 0.8 V or open).

	Unit		>	=	=	=	=	=	=	=	=	=	=	=	=	=	=	=	=	=	=	= =	: =	=	=	μA	=	= =		-	: =	=	=	=			=	= :		=
	Limits	Max									0.55	=	=	=	=	=	=	=	-1.2	=	=		: =	=	=	20	=		:	=	: :	=	100	=		ш	=			=
		Min	2.5	=	=	=	=	=	=	=																														
	Measured		12	ΙΣ	12	12	<u>Y2</u>	<u>Y2</u>	<u>Y2</u>	<u>Y2</u>	ΙΣ	ΙΣ	ΙΣ	15	<u>Y2</u>	<u>Y2</u>	<u>Y2</u>	<u>Y2</u>	A1	B1	CJ	5 6	20 2	200	A2	A1	B1	5 2	ב	70	22 6	D2 A2	A2	B1	C1	D1	D2	C5	B2	A2
41	20	Vcc	4.5 V	=	=	=		=	=	=	=	=	=	=	=	=	=	=		=	=	= :	: =	=	=	5.5 V	=	= :	: =		: =	=	=		н	н	=	= :		:
13	19	A2	5.5 V	=	=	=	=	=	=	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V		=		: =	=	-18 mA							7.7.0	۷.7.							7.0 V
12	18	B2	5.5 V	=	=	=	=	=	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V		=	=	= =	: =	ν α	5.5 V						7.4.0	> / >						-	7.0 V	
11	16	NC)															-	_
10	14	C2	5.5 V	=	=	=	=	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V	=		=		= =	. 07	-10 IIIA	5.5 V					1	2.7 V							7.0 /	-	
6	13	D2	5.5 V	=	=	-	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V	=	=	=	=	=	= (-18 mA	+	=				7	7.7							7.0 V		1	_
8	12	<u>Y2</u>					-1.0 mA	=	=	=					48 mA	=	=	=					•																	_
7	10	GND	GND	,	n	n	ŋ	3	,,	,	=	3	3	3	n	,	n	3	n	n	я	n	: 3	n	ņ	n	n	n	: 3		: 3	n	31	11	"	n	n	3	,	:
9	6	ΙΣ	-1.0 mA	=	=	=					48 mA	=	=	=																										
2	8	Ы	5.5 V	=	=	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V	=	=	=		=	=	-18 mA	2.5 \	=	=			1	2.7 V							7.0 V				
4	9	ည	5.5 V	5.5 V	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V	=	=	=	=		=	-18 mA	_	: =	=	=			2.7 V							7.0 V					
က	4	NC																			•																			_
2	3	B1	5.5 V	0.8 V	5.5 V	=	=	=	=	=	=	2.0 V	5.5 V	=	=	=	=	=	=	-18 mA	5.5 V	= :	: =	=	=		2.7 V							7.0 V						_
-	2	P4	V 8.0	5.5 V	=	=	=	=	=	=		5.5 V	=	=	=	=	=	=	_	5.5 V -′		= =	: =	=	=	2.7 V							7.0 V	\vdash				1	+	
Cases	Case <u>1/</u>	Test no.	-	2	3	4	2	9	7	8	6	10	11	12	13	14	15	16			19	50	17.	23	24		26	27	87 88	67	30	32	33	34	35	36	37	38	39	40
OF O	883 method	<u> </u>	3006	=	=	=	=	=	=	=	3007	=	=	=	=	=	=	=		,				_1		3010	=		: =		<u> </u>	=	=	<u>-</u> -	=	=				:
	Symbol		V _{он}								Vol								Vıc							표							<u>-</u>	4						
	Subgroup		1	$Tc=25^{\circ}C$							•																						•							

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 03 – Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V or low ≤ 0.8 V or open).

	Unit			mA	=	=	=	=	H	=	=	=	=	н																				su	я	=	=	=	=	=	=
	iits		Мах	7/		=	=	=	=	=	=	-255	-255	17	4																			5.5	n	=	=	=	=	=	=
	Limits		Min	/7	н		н				н	-100	-100																					1.0	n		=	=	=	н	=
	Measured	terminal		A1	B1	5	D1	D2	C2	B2	A2	7.	<u>Y2</u>	Vcc	Vcc			Η	outputs	=			=	=		=		=		=	"	"	"	A1 to 71	B1 to 71	C1 to 71	D1 to 71			B2 to <u>Y2</u>	A2 to <u>Y2</u>
14	20		ر ا	5.5 V	н	=	=	=	=	=	=	=	=		н			3	н	н	н	н		н	н	н			н	н	н	н	н	5.0 V	=	=	=	=	=	=	=
13	19	!	A2	5.5 V		=	=	=	=	=	0.5 V	5.5 V	0.0 V	5.5 V	0.0 V			В	Α	В	Α	В	Α	В	Α	В	А	В	Α	В	Α	В	Α					2.7 V		=	Z
12	18		B2	5.5 V		=	=	=	=	0.5 V	5.5 V	5.5 V	0.0 V	5.5 V	0.0 V			В	В	Α	Α	В	В	Α	Α	В	В	Α	Α	В	В	Α	Α					2.7 V	2.7 V	Z	2.7 V
11	16		S																																						
10	14		C5	5.5 V	=	:	=	=	0.5 V	5.5 V	=	=	0.0 V	5.5 V	0.0 V			В	=		н	Α	=		н	В		=		A			н					2.7 V	Z	2.7 V	2.7 V
6	13	!	D2	5.5 V	=	=	=	0.5 V	5.5 V	=	=	=	0.0 V	5.5 V	0.0 V			В	=		н	н	=		н	٧	ш	=	н		н		н					Z	2.7 V	=	=
8	12	ļ	<u>۲</u> ۲										0.0 V			itted.	ed.	I	=	н	н	н		н	н	H			н	н	ш		٦					OUT	=	=	=
7	10		GND	GND	n	n	n	n	n	n	n	=	n n	n	n	and V _{IC} tests are omitted.	55°C and V _{IC} tests are omitted.	GND	n		n	,,	n	n	n	n	11	n	n	n	n	n	19	=	n	=	=	=	=	=	=
9	6	1	5									0.0 V				ind V _{IC} tes	I V _{IC} tests	エ	=		н	н			н				н		ш	=		OUT	=	=	=				
2	∞		5	5.5 V		=	0.5 V	5.5 V	=	=	=	0.0 V	5.5 V	5.5 V	0.0 V	25°C	°C an	В			"				"	A			"		"			2.7 V	=	=	Z				
4	9	,	ပ	5.5 V	5.5 V	0.5 V	5.5 V	=	=		=	0.0 V	5.5 V	5.5 V	0.0 V	cept T _c =	cept T _c =	В			"	Α			"	В			"	Α				2.7 V	2.7 V	Z	2.7 V				
3	4		S													oup 1, ex	oup 1, ex																								
2	က	ı	B4	5.5 V	0.5 V	5.5 V	=	=	=	=	=	0.0 V	5.5 V	5.5 V	0.0 V	for subgr	for subgr	В	В	A	Α	В	В	A	Α	В	В	Α	Α	В	В	Α	Α	2.7 V	Z	2.7 V	2.7 V				
1	2	I	¥	0.5 V	5.5 V			=	=	=	=	0.0 V	5.5 V	5.5 V	0.0 V	d limits as	d limits as	В	Α	В	Α	В	Α	В	Α	В	Α	В	Α	В	Α	В	Α	Z	2.7 V	=	=				
Cases	Case 1/	2	Test no.	41	42	43	44	45	46	47	48	49	20	51	52	onditions an	onditions an	53	54	22	99	22	28	69	09	61	62	63	64	92	99	67	68	69	20	7.1	72	73	74	75	92
		method		3009	=	=	=	=	=	=	=	3011	3011	3005	3005	Same tests, terminal conditions and limits as for subgroup 1, except T_{C}	s, terminal cu	3014	=	=	=	=	=	=	=	-	=	=	=	=	=	=		t _{PLH} 3003 69 IN 2.7 V	Fig. 3	=	=	=	=	=	=
	Symbol	<u> </u>		_=								sol		lccl	lccH	Same test	Same test	Func-	tional	tests	41													фн							
	Subgroup	_		1	$Tc = 25^{\circ}C$							•		•	•		က		$Tc = 25^{\circ}C$															6	$Tc = 25^{\circ}C$						

See footnotes at end of device type 03.

TABLE III. Group A inspection for device type 03 – Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V or low ≤ 0.8 V or open).

		MIL-STD-	Cases C,D	-	2	3	4	2	9	7	∞	တ	9		12	13	4				
dnc	Subgroup Symbol	883 method	Case <u>1/</u> 2	7	3	4	9	80	6	10	12	13	41	16	18	19	20	Measured terminal	Limits	ıts	Unit
			Test no.	A1	B1	S	ပ	Ы	ΙΣ	GND	<u>72</u>	D2	C2	NC	B2	A2	Vcc		Min	Max	
6	t _{PHL}	3003	22	Z	2.7 V		2.7 V	2.7 V	OUT	=							5.0 V	A1 to 71	1.0	4.5	su
Tc = 25°C		Fig. 3	78	2.7 V	≥		2.7 V	=	=	3							=	B1 to ₹1	31	3	я
		=	62	=	2.7 V		Z	=	=	=							=	C1 to 77	=	=	=
		=	80		2.7 V		2.7 V	Z	=	=								D1 to 71	=	=	=
		=	81							=	OUT	Z	2.7 V		2.7 V	2.7 V	=	D2 to $\overline{\text{Y2}}$	=	=	=
		=	82							=	=	2.7 V	Z		2.7 V	н		C2 to $\overline{\text{Y2}}$	=	=	=
		=	83							=			2.7 V		Z	н		B2 to <u>Y2</u>	ш	=	ш
		=	84							=	=	=	2.7 V		2.7 V	N		A2 to $\overline{\text{Y2}}$	=	=	=
10 S	Same tes	Same tests and terminal conditions as for subgroup 9, except $T_{\rm C}$ =	nal condition	is as for si	ubgroup 9,	except T	₂ = +125°	C and us	+125° C and use limits from table	im table I.											
11	Same tes	ts terminal c	Same tests terminal contitions and limits as for subdrough extent 7. = .55° C.	nd limits a	s for subar	oup 10. e.	xcent T _c =	55° C													

1/ For case 2, pins not referenced are N/C.

 $\underline{2}/\ l_{\rm lL}$ limits mA minimum/maximum values for circuits as shown:

	0/-1.2		50/-1.2	П
Circuit [Circuit C	Circuit B	Circuit A	Parameters

 $\underline{3}/$ Perform function sequence at V_{cc} = 4.5 V and repeat at V_{cc} = 5.5 V.

 $\underline{4}/$ A = 2.5 V minimum, B = 0.55 V or GND, H \geq 2.5 V, L \leq 0.5 V.

5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Service or Defense Agency, or within the military service's system command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

- 6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.
 - 6.2 Acquisition requirements. Acquisition documents should specify the following:
 - a. Title, number, and date of the specification.
 - b. PIN and compliance identifier, if applicable (see 1.2).
 - c. Requirements for delivery of one copy of the conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
 - f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - i. Requirements for "JAN" marking.
 - j. Packaging requirements (see 5.1).
- 6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.
- 6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential
I _{IN}	Current flowing into an input terminal
V _{IN}	Voltage level at an input terminal

- 6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.
- 6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-35810 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device	Generic-industry
type	type
01	54F37
02	54F38
03	54F40

6.8 <u>Manufacturers' designation.</u> Manufacturers' circuits which form a part of this specification are designated with an "X" as shown in table IV herein.

TABLE IV. Manufacturers' designations.

		Circuit		
Device	А	В	С	D
type	National Semiconductor/ Fairchild Semiconductor	Motorola Inc.	Signetics	Texas Instrument
01	Χ		Х	
02	Χ		Х	
03	X			

6.9 <u>Changes from previous issue.</u> Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Preparing activity: DLA - CC Custodians:

Army - CR Navy - EC Air Force - 11 (Project 5962-2045) DLA - CC

Review activities:

Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at www.dodssp.daps.mil.